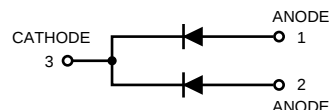
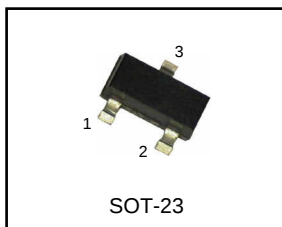


Monolithic Dual Switching Diode Common Cathode



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	VR	70	Vdc
Peak Forward Current	IF	200	mAdc
Peak Forward Surge Current	IFM(surge)	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max.	Unit
Total Device Dissipation FR-5 Board ⁽¹⁾ TA=25°C Derate above 25°C	PD	225 1.8	mW mW / °C
Thermal Resistance, Junction to Ambient	RθJA	556	°C / W
Total Device Dissipation Alumina Substrate, ⁽²⁾ TA=25°C Derate above 25°C	PD	300 2.4	mW mW / °C
Thermal Resistance, Junction to Ambient	RθJA	417	°C / W
Junction and Storage Temperature	TJ,TSTG	-55 to +150	°C

DEVICE MARKING

BAV70=A4

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min.	Max.	Unit
----------------	--------	------	------	------

OFF CHARACTERISTICS

Reverse Breakdown Voltage (IBR=100uAdc)		V(BR)	70	-	Vdc
Forward Voltage	(IF=1.0 mAdc)	VF	-	715	mVdc
	(IF=10 mAdc)		-	855	
	(IF=50 mAdc)		-	1000	
	(IF=150 mAdc)		-	1250	
Reverse Voltage Leakage Current	(VR=70 Vdc)	IR	-	2.5	uAdc
	(VR=25 Vdc, TJ=150°C)		-	60	
	(VR=70 Vdc, TJ=150°C)		-	100	
Diode Capacitance (VR=0, f=1.0MHZ)		CJ	-	1.5	pF
Reverse Recovery Time (IF=IR=10 mAdc, VR=5.0 Vdc, IR(REC)=1.0mAdc, RL=100Ω)		trr	-	6.0	nS

(1) FR-5=1.0 x 0.75 x 0.062in.

(2) Alumina=0.4 x 0.3 x 0.024in. 99.5% alumina.

FIGURE 1. RECOVERY TIME EQUIVALENT TEST CIRCUIT

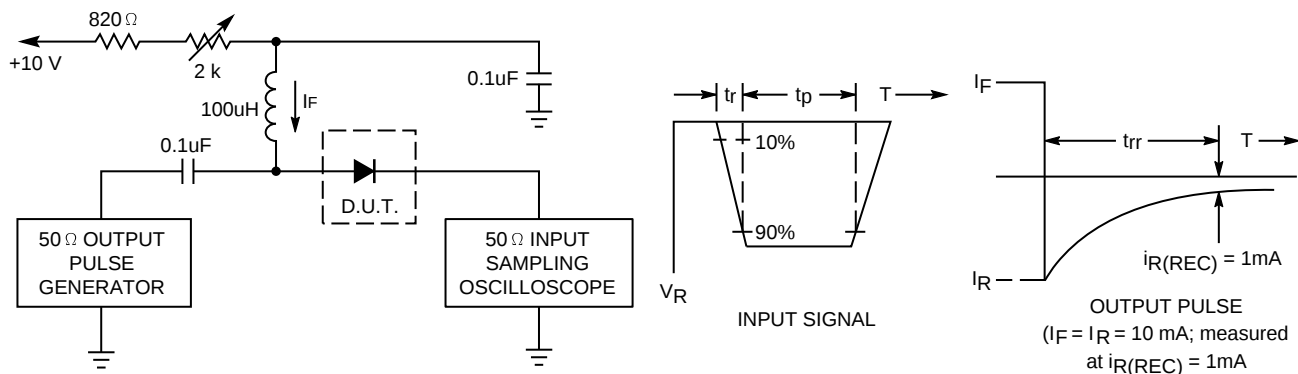


FIGURE 2. FORWARD VOLTAGE

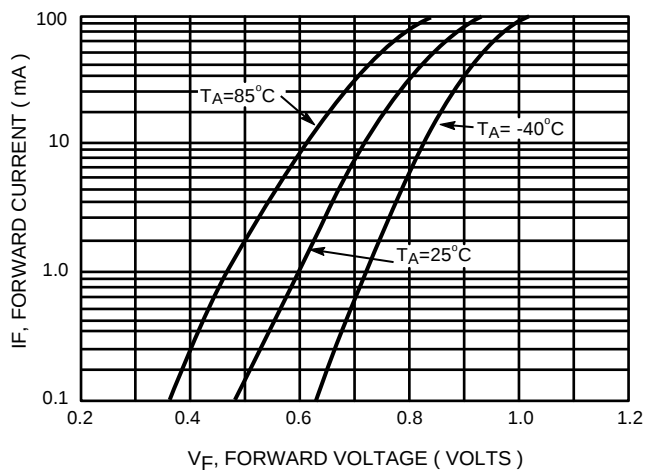


FIGURE 3. LEAKAGE CURRENT

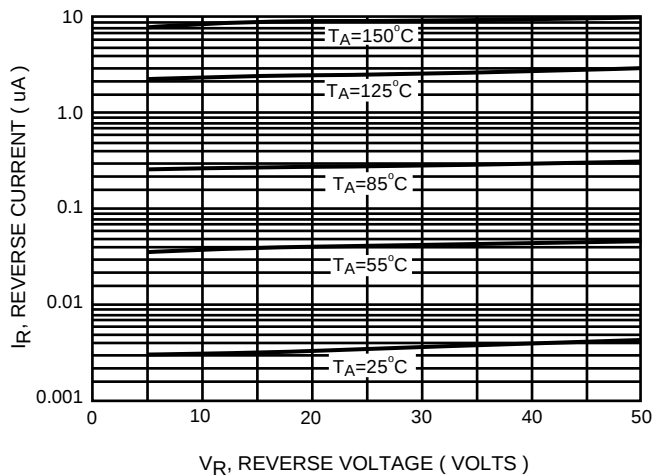


FIGURE 4. CAPACITANCE

